

Amendments to the Claims

This listing of claims replaces all prior versions and listings of claims in the application.

Listing of Claims

1-9. (Canceled)

10. (Currently Amended) A method of manufacturing a semiconductor device comprising:

forming a first wiring on a same layer as a source or drain electrode over a substrate;

forming an insulating film over the first wiring;

forming a plurality of contact holes in the insulating film; and

forming a second wiring over the insulating film,

wherein the first wiring is in contact with the second wiring via the plurality of contact holes, and

wherein the first wiring extends in parallel with the second wiring.

11. (Previously Presented) A method of manufacturing a semiconductor device according to claim 10, wherein the insulating film comprises an organic resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

12. (Currently Amended) A method of manufacturing a semiconductor device according to claim 10, wherein the first wiring comprises ~~at least one selected from the group consisting of~~ aluminum, tantalum, ~~polycrystalline silicon, and tungsten silicide.~~

13. (Currently Amended) A method of manufacturing a semiconductor device according to claim 10, wherein ~~the second wiring comprises aluminum~~ the insulating film comprises an interlayer insulating film.

14. (Previously Presented) A method of manufacturing a semiconductor device according to claim 10, wherein the semiconductor device is at least one of a liquid crystal display device and an electroluminescence display device.

15. (Currently Amended) A method of manufacturing a semiconductor device comprising:

forming a gate electrode over a substrate;

forming a first insulating film over the gate electrode;

forming a first wiring on a same layer as a [[gate]] source or drain electrode over a substrate the first insulating film;

forming [[an]] a second insulating film over the first wiring ~~and the gate electrode;~~

forming a plurality of contact holes in the second insulating film; and

forming a second wiring ~~on a same layer as a source or drain electrode~~ over the second insulating film,

wherein the first wiring is in contact with the second wiring via the plurality of contact holes, and

wherein the first wiring extends in parallel with the second wiring.

16. (Previously Presented) A method of manufacturing a semiconductor device according to claim 15, wherein the insulating film comprises an organic resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

17. (Currently Amended) A method of manufacturing a semiconductor device according to claim 15, wherein the first wiring comprises ~~at least one selected from the group consisting of aluminum, tantalum, polycrystalline silicon, and tungsten silicide.~~

18. (Currently Amended) A method of manufacturing a semiconductor device according to claim 15, wherein ~~the second wiring comprises aluminum each of the first insulating film and the second insulating film comprises an interlayer insulating film.~~

19. (Previously Presented) A method of manufacturing a semiconductor device according to claim 15, wherein the semiconductor device is at least one of a liquid crystal display device and an electroluminescence display device.

20. (Currently Amended) A method of manufacturing a semiconductor device comprising:

forming a first wiring and a third wiring in a driving circuit over a substrate;
forming an insulating film over the first wiring and the third wiring;
forming a plurality of contact holes in the insulating film; and
forming a second wiring in the driving circuit over the insulating film,
wherein the first wiring is in contact with the second wiring via the plurality of contact holes, [[and]]
wherein the first wiring extends in parallel with the second wiring, and
wherein the second wiring intersects with the third wiring.

21. (Previously Presented) A method of manufacturing a semiconductor device according to claim 20, wherein the insulating film comprises an organic resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

22. (Previously Presented) A method of manufacturing a semiconductor device according to claim 20, wherein the first wiring comprises at least one selected from the group consisting of aluminum, tantalum, polycrystalline silicon, and tungsten silicide.

23. (Previously Presented) A method of manufacturing a semiconductor device according to claim 20, wherein the second wiring comprises aluminum.

24. (Previously Presented) A method of manufacturing a semiconductor device according to claim 20, wherein the semiconductor device is at least one of a liquid crystal display device and an electroluminescence display device.

25. (Currently Amended) A method of manufacturing a semiconductor device comprising:

forming a first wiring and a third wiring in a driving circuit on a same layer as a gate electrode over a substrate;

forming an insulating film over the first wiring, the third wiring and the gate electrode;

forming a plurality of contact holes in the insulating film; and

forming a second wiring in the driving circuit on a same layer as a source or drain electrode over the insulating film,

wherein the first wiring is in contact with the second wiring via the plurality of contact holes, [[and]]

wherein the first wiring extends in parallel with the second wiring, and

wherein the second wiring interests with the third wiring.

26. (Previously Presented) A method of manufacturing a semiconductor device according to claim 25, wherein the insulating film comprises an organic resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

27. (Previously Presented) A method of manufacturing a semiconductor device according to claim 25, wherein the first wiring comprises at least one selected from the group consisting of aluminum, tantalum, polycrystalline silicon, and tungsten silicide.

28. (Previously Presented) A method of manufacturing a semiconductor device according to claim 25, wherein the second wiring comprises aluminum.

29. (Previously Presented) A method of manufacturing a semiconductor device according to claim 25, wherein the semiconductor device is at least one of a liquid crystal display device and an electroluminescence display device.

30. (Currently Amended) A method of manufacturing a semiconductor device comprising:

forming a first wiring and a third wiring in a source line driving circuit over a substrate;
forming an insulating film over the first wiring and the third wiring;
forming a plurality of contact holes in the insulating film; and
forming a second wiring in the source line driving circuit over the insulating film,
wherein the first wiring is in contact with the second wiring via the plurality of contact holes, [[and]]

wherein the first wiring extends in parallel with the second wiring, and
wherein the second wiring intersects with the third wiring.

31. (Previously Presented) A method of manufacturing a semiconductor device according to claim 30, wherein the insulating film comprises an organic resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

32. (Previously Presented) A method of manufacturing a semiconductor device according to claim 30, wherein the first wiring comprises at least one selected from the group consisting of aluminum, tantalum, polycrystalline silicon, and tungsten silicide.

33. (Previously Presented) A method of manufacturing a semiconductor device according to claim 30, wherein the second wiring comprises aluminum.

34. (Previously Presented) A method of manufacturing a semiconductor device according to claim 30, wherein the semiconductor device is at least one of a liquid crystal display device and an electroluminescence display device.

35. (Currently Amended) A method of manufacturing a semiconductor device comprising:

forming a first wiring and a third wiring in a source line driving circuit on a same layer as a gate electrode over a substrate;

forming an insulating film over the first wiring, the third wiring and the gate electrode;

forming a plurality of contact holes in the insulating film; and

forming a second wiring in the source line driving circuit on a same layer as a source or drain electrode over the insulating film,

wherein the first wiring is in contact with the second wiring via the plurality of contact holes, [[and]]

wherein the first wiring extends in parallel with the second wiring, and

wherein the second wiring intersects with the third wiring.

36. (Previously Presented) A method of manufacturing a semiconductor device according to claim 35, wherein the insulating film comprises an organic resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

37. (Previously Presented) A method of manufacturing a semiconductor device according to claim 35, wherein the first wiring comprises at least one selected from the group consisting of aluminum, tantalum, polycrystalline silicon, and tungsten silicide.

38. (Previously Presented) A method of manufacturing a semiconductor device according to claim 35, wherein the second wiring comprises aluminum.

39. (Previously Presented) A method of manufacturing a semiconductor device according to claim 35, wherein the semiconductor device is at least one of a liquid crystal display device and an electroluminescence display device.